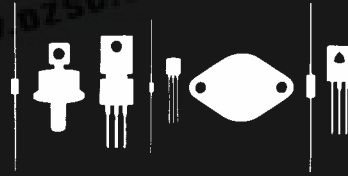


Central Semiconductor Corp.
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 145 Adams Avenue
 Hauppauge, New York 11788



2N3641 PN3641
 2N3642 PN3642
 2N3643 PN3643

JEDEC TO-105 JEDEC TO-92

NPN SILICON SIGNAL TRANSISTORS

DESCRIPTION

The CENTRAL SEMICONDUCTOR 2N3641, PN3641 Series types are Silicon NPN Small Signal Transistors designed for general purpose amplifier applications.

MAXIMUM RATINGS (TA=25°C)

	SYMBOL	2N3641	2N3642	UNIT
		2N3643	PN3642	
Collector-Base Voltage	VCBO	60	60	V
Collector-Emitter Voltage	VCEO	30	45	V
Emitter-Base Voltage	VEBO	5.0	5.0	V
Collector Current	IC	500	500	mA
Power Dissipation	PD	350	625	mW
Operating and Storage Junction Temperature	TJ, Tstg	-55 TO +125	-55 TO +150	°C

ELECTRICAL CHARACTERISTICS (TA=25°C)

SYMBOL	TEST CONDITIONS	2N3641	2N3642	2N3643	UNIT
		PN3641	PN3642	PN3643	
ICES	VCE=50V		50	50	nA
BVCB0	IC=10µA	60	60	60	V
BVCE0	IC=10µA	60	60	60	V
BVCEO	IC=10mA	30	45	30	V
BVEBO	IE=10µA	5.0	5.0	5.0	V
VCE(SAT)	IC=150mA, IB=15mA	0.22	0.22	0.22	V
hFE	VCE=10V, IC=150mA	40	120	100	300
hFE	VCE=10V, IC=500mA	15	15	25	
fT	VCE=5.0V, IC=50mA, f=100MHz	150	150	250	MHz
Cob	VCB=10V, f=140kHz		8.0	8.0	pF
Gpe	VCE=15V, RG=140Ω, RL=260Ω, f=30MHz, PIN=40mW	10	10	10	dB
η	VCE=15V, RG=140Ω, RL=260Ω, f=30MHz, PIN=40mW	60	60	60	%
ton	IC=300mA, IB1=30mA	60	60	60	ns
toff	IC=300mA, IB1=IB2=30mA	150	150	150	ns